

- [23] 2015/03/29@Nagoya in Japan
ISPlasma2015/IC-PLANTS2015
Plasma-assisted polishing for damage-free atomically flat finishing of wide gap semiconductor materials
OK. Yamamura, H. Deng, K. Endo

- [22] 2014/10/19@Jiaozuo in China
The 10th China-Japan International Conference on Ultra-Precision Machining Process (CJUMP) and 2014 International Conference on Surface Finishing Technology (ICSFT)
Flattening of 4H-SiC by combination of oxidation and abrasive polishing
OH. Deng, K. Endo, K. Yamamura

- [21] 2014/10/19@Jiaozuo in China
The 10th China-Japan International Conference on Ultra-Precision Machining Process (CJUMP) and 2014 International Conference on Surface Finishing Technology (ICSFT)
Ultra-precision deterministic figuring by pulse width modulation controlled plasma jet figuring
OK. Yamamura, Y. Takeda, S. Sakaiya, K. Endo

- [20] 2014/09/25@Hawaii in USA
The 17th International Symposium on Advances in Abrasive Technology (ISAAT2014)
Preliminary study on highly efficient polishing of 4H-SiC utilizing anodic oxidation
OK. Yamamura, K. Hosoya, Y. Imanishi, H. Deng, K. Endo

- [19] 2014/09/19@Garmisch-Partenkirchen in Germany
14th International Conference on Plasma Surface Engineering (PSE2014)
Surface modification of PTFE for a high adhesive Ag layer by open-air type plasma treatment with graft copolymerization
OH. Sato, K. Ishihara, Y. Ohkubo, K. Endo, K. Yamamura

- [18] 2014/09/08@Madrid in Spain
International Conference on Diamond and Carbon Materials 2014
Highly efficient planarization of CVD-grown single-crystal diamond substrate by atmospheric-pressure microwave plasma jet figuring
OK. Yamamura, S. Makiyama, T. Tabata, H. Yamada, A. Cyayahara, Y. Mokuno, S. Shikata, K. Endo

- [17] 2014/09/09@Nara in Japan
5th World Congress on Adhesion and Related Phenomena(WCARP-V)
Formation of highly adhesive polytetrafluoroethylene /isobutylene-isoprene rubber interface by atmospheric-pressure plasma irradiation
OK. Ishihara, H. Sato, Y. Ohkubo, M. Shibahara, A. Nagatani, K. Honda, K. Endo, K. Yamamura

- [16] 2014/08/27@Nantes in France
64th CIRP General Assembly
Optimization of the plasma oxidation and abrasive polishing processes in plasma-assisted polishing for highly effective planarization of 4H-SiC
OH. Deng, K. Monna, T. Tabata, K. Endo, K. Yamamura
- [15] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Improvement of spatial resolution in figuring using open-air type plasma chemical vaporization machining with pulse width modulation control
OY. Takeda, Y. Hata, J. Ito, K. Endo, K. Yamamura
- [14] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Effect of plasma irradiation in removal rate of single crystal diamond in plasma assisted polishing with quartz glass tool
OT. Tabata, K. Monna, Y. Yamamoto, S. Makiyama, H. Deng, K. Endo, K. Yamamura
- [13] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Surface modification of PTFE for a high adhesive Cu layer by open-air type plasma treatment with graft copolymerization
OH. Sato, K. Ishihara, Y. Ohkubo, K. Endo, K. Yamamura
- [12] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Dependency of OH emission intensity in material removal rate of sapphire substrates in plasma assisted polishing
OK. Monna, H. Deng, T. Tabata, K. Endo, K. Yamamura
- [11] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Two-stage precision figuring process applying numerically controlled electrochemical machining with suction type electrode
ON. Mitsushima, M. Ouchi, K. Endo, K. Yamamura
- [10] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Investigation of the anodic oxide layer/SiC interface morphology during anodic oxidation assisted polishing
OK. Hosoya, Y. Imanishi, K. Endo, K. Yamamura

- [09] 2014/07/24@Kanazawa in Japan
The 15th International Conference on Precision Engineering (ICPE2014)
Surface modification of GaN by irradiation of atmospheric pressure plasma for damage-free polishing
O.H. Deng, K. Endo, K. Yamamura

- [08] 2014/07/15@Tsukuba in Japan
The 2nd International Symposium on Science at J-PARC
Ultra-precision fabrication process for neutron focusing device
OK. Yamamura, N. Mitsushima, Y. Goto, K. Endo, D. Yamazaki, R. Maruyama, H. Hayashida, K. Soyama

- [07] 2014/06/27@Hawaii in USA
ASPE/ASPEN Summer Topical Meeting
Systematic error analysis of nanop profiler using normal vector tracing method based on numerical simulation
OR. Kudo, K. Okuda, K. Okita, Y. Tokuta, M. Nakano, K. Yamamura, K. Endo

- [06] 2014/06/27@Hawaii in USA
ASPE/ASPEN Summer Topical Meeting
A nanop profiler using the normal vector tracing method for high accuracy aspheric mirrors
OR. Kudo, K. Endo

- [05] 2014/06/25@Hawaii in USA
Optical Fabrication and Testing, Classical Optics 2014
Measurement of high accurate mirror using nanop profiler with self-calibratable rotary encoder
OK. Okita, T. Kojima, K. Usuki, K. Okuda, Y. Tokuta, M. Nakano, R. Kudo, K. Yamamura, K. Endo

- [04] 2014/06/05@Dubrovnik in Croatia
14th International Conference of the European Society for Precision Engineering and Nanotechnology
Flatness correction of quartz glass substrate by plasma jet figuring with pulse width modulation control
OK. Yamamura, Y. Takeda, Y. Hata, J. Ito, K. Endo

- [03] 2014/06/05@Dubrovnik in Croatia
14th International Conference of the European Society for Precision Engineering and Nanotechnology
Polishing characteristics of single crystal SiC assisted by plasma oxidation using different kinds of abrasives
O.H. Deng, K. Endo, K. Yamamura

- [02] 2014/05/29@Nottingham in UK
2nd CIRP Conference on Surface Integrity (CSI)
Study on oxidation processes of 4H-SiC (0001) for investigation of the atomically flattening mechanism in plasma assisted polishing
O.H. Deng, K. Yamamura
- [01] 2014/04/21@San Francisco in USA
2014 MRS Spring Meeting & Exhibit
Undulator synchrotron X-ray-induced reduction of Au ions to metals in an aqueous solution and in situ time-resolved DXAFS
O.T. Nakagawa, Y. Ohkubo, T. Okazaki, S. Seino, T.A. Yamamoto, H. Nitani, Y. Niwa